

## 长春新产业光电技术有限公司

Changchun New Industries Optoelectronics Tech, Co., Ltd,

DATA SHEET

R1040.10 and 1040.11 romics Tech. Co., Ltd. (CNI) one, Changchun, China

EO-266-P-Subnano/1~110uJ

## HIGH ENERGY DIODE PUMPED ALL-SOLID-STATE Q-SWITCHED LASER

SPECIFICATIONS

High energy diode pumped all solid state Q-switched laser at 266nm has the features of high single pulse energy, short pulse duration, and high peak power, which is widely used in Lidar, biomedicine, environmental monitoring, scientific research, and so on.



266±1	
Q-switched: PM (Passive Modulation)	1
110	
<1	
500Hz, 1kHz, 2kHz optional, EXT	
<5%, <4%	
TEM <sub>00</sub>	7/10
≤1.5	
<3	]
~3	AVOID EXPOSURE: Laser radiation is en
<15	DANGE
67	
Air cooled	LASER RADIATION-AVOID DIF
15~30	CLASS IIIb LASER P This device complies with 21 CFB
PSU-DPS-Subnano	Changchun New Industries Optoelectr No 588 Jinhu Road, High-tech Zo
l year	
	Q-switched: PM (Passive Modulation)   110   <1

